

## LC<sup>2</sup>MOS Quad SPST Switches

## ADG211A/ADG212A

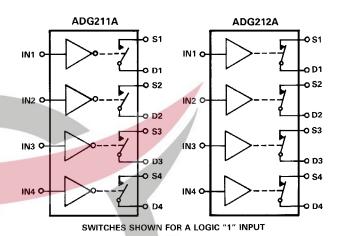
#### **FEATURES**

44V Supply Maximum Rating
±15V Analog Signal Range
Low R<sub>ON</sub> (115Ω max)
Low Leakage (0.5nA typ)
Break Before Make Switching
Single Supply Operation Possible
Extended Plastic Temperature Range
(-40°C to +85°C)
TTL/CMOS Compatible
Available in 16-Lead DIP/SOIC and
20-Lead PLCC Packages
Superior Second Source:
ADG211A Replaces DG211
ADG212A Replaces DG212

### **GENERAL DESCRIPTION**

The ADG211A and ADG212A are monolithic CMOS devices comprising four independently selectable switches. They are designed on an enhanced LC<sup>2</sup>MOS process which gives an increased signal handling capability of  $\pm 15$ V. These switches also feature high switching speeds and low  $R_{ON}$ .

The ADG211A and ADG212A consist of four SPST switches. They differ only in that the digital control logic is inverted. In multiplexer applications, all switches exhibit break-before-make switching action when driven simultaneously. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.



### PRODUCT HIGHLIGHTS

- Extended Signal Range:
   These switches are fabricated on an enhanced LC<sup>2</sup>MOS process, resulting in high breakdown and an increased analog signal range of ± 15V.
- Single Supply Operation:
   For applications where the analog signal is unipolar (0V to 15V), the switches can be operated from a single + 15V supply.
- 3. Low Leakage:

Leakage currents in the range of 500pA make these switches suitable for high precision circuits. The added feature of Break before Make allows for multiple outputs to be tied together for multiplexer applications while keeping leakage errors to a minimum.

	ADG211A IN	ADG212A IN	SWITCH CONDITION
E	of C	RON	ON OFF

Table I. Truth Table

### REV. B

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# ADG211A/ADG212A—SPECIFICATIONS $(V_{DD} = +15V, V_{ss} = -15V, V_L = 5V, unless otherwise noted.)$

		ADG211AKN ADG212AKN			
Parameter	25°C	-40°C to +85°C	Units	Test Conditions	
ANALOGSWITCH					
Analog Signal Range	± 15	± 15	Volts		
$R_{ON}$	115	175	Ωmax	$-10V \le V_S \le +10V, I_{DS} = 1 \text{mA},$ Test Circuit 1	
$R_{ON}$ vs. $V_{D}(V_{S})$	20		% typ		
R <sub>ON</sub> Drift	0.5		%/°C typ		
R <sub>ON</sub> Match	5		% typ	$V_S = 0V, I_{DS} = 1mA$	
$I_{S}(OFF)$	0.5		nA typ	$V_D = \pm 14V$ ; $V_S = \mp 14V$ ; Test Circuit 2	
OFF Input Leakage	5	100	nA max		
$I_{\mathbf{D}}(\mathbf{OFF})$	0.5		nA typ	$V_D = \pm 14V$ ; $V_S = \mp 14V$ ; Test Circuit 2	
OFF Output Leakage	5	100	nA max	,	
$I_{D}(ON)$	0.5		nA typ	$V_D = V_S = \pm 14V$ ; Test Circuit 3	
ON Channel Leakage	5	200	nA max	, b , s = 1, s s s s s s s s s	
DIGITAL CONTROL	4				
V <sub>INH</sub> , Input High Voltage		2.4	V min	TTL Compatibility is Independent of V <sub>I</sub>	
V <sub>INL</sub> , Input Low Voltage		0.8	V max	T TE compationity is independent of $V_{\rm L}$	
I <sub>INL</sub> or I <sub>INH</sub>		1	μA max		
C <sub>IN</sub> , Digital Input Capacitance	5		pF typ		
DYNAMIC CHARACTERISTICS	7				
t <sub>OPEN</sub> <sup>1</sup>	30		ns typ	Test Circuit 4	
ton <sup>1</sup>	600		ns max	Test Circuit 5	
t <sub>OFF</sub> <sup>1</sup>	450		ns max	Test Circuit 5	
OFF Isolation	80		dB typ	$V_S = 10V(p-p); f = 100kHz$	
				$R_L = 75\Omega$ ; Test Circuit 6	
Channel-to-Channel Crosstalk	80		dB typ	Test Circuit 7	
$C_{S}(OFF)$	5		pF typ		
$C_{\mathbf{D}}(\mathbf{OFF})$	5		pF typ		
$C_{S}, C_{D}(ON)$	16		pF typ		
Q <sub>INJ</sub> , Charge Injection	20		pC typ	$R_S = 0\Omega$ ; $C_L = 1000 pF$ ; $V_S = 0V$ Test Circuit 8	
POWER SUPPLY					
$I_{DD}$	0.6		mA typ	Digital Inputs = V <sub>INL</sub> or V <sub>INH</sub>	
$I_{DD}$	1		mA max		
I <sub>ss</sub>	0.1	_	mA typ		
$I_{SS}$	0.2		mA max		
IL	0.9		mA max		

NOTE

<sup>1</sup>Sample tested at 25°C to ensure compliance.

Specifications subject to change without notice.



## ADG211A/ADG212A

ABSOLUTE MAXIMUM RATINGS*	Digital Inputs <sup>1</sup>
$(T_A = 25^{\circ}C \text{ unless otherwise stated})$	Voltage at IN $V_{SS}$ –2V to
	$V_{\mathrm{DD}} + 2V  \mathrm{or}$
$V_{DD}$ to $V_{SS}$	20mA, Whichever Occurs First
$V_{DD}$ to GND	Power Dissipation (Any Package)
$V_{SS}$ to GND	Up to $+75^{\circ}$ C 470mW
$V_L$ to GND	Derates above +75°C by 6mW/°C
Analog Inputs <sup>1</sup>	Operating Temperature $-40^{\circ}$ C to $+85^{\circ}$ C
Voltage at S, D $V_{SS} - 0.3V$ to $V_{DD} + 0.3V$	Storage Temperature Range $-65^{\circ}$ C to $+150^{\circ}$ C
Continuous Current, S or D 30mA	Lead Temperature (Soldering 10sec) + 300°C
Pulsed Current S or D	NOTE
1ms Duration, 10% Duty Cycle 70mA	<sup>1</sup> Overvoltage at IN, S or D will be clamped by diodes. Current should be limited to the Maximum Rating above.

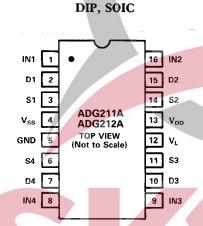
<sup>\*</sup>COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one Absolute Maximum Rating may be applied at any one time.

### CAUTION

ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are removed.



### **PIN CONFIGURATIONS**





### **ORDERING GUIDE**

# ELECTRONIC

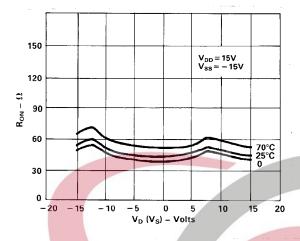
Model	Temperature Range	Package Option*
ADG211AKN	-40°C to +85°C	N-16
ADG211AKR	$-40^{\circ}$ C to $+85^{\circ}$ C	R-16A
ADG211AKP	$-40^{\circ}\text{C to} + 85^{\circ}\text{C}$	P-20A
ADG212AKN	-40°C to +85°C	N-16
ADG212AKR	$-40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	R-16A
ADG212AKP	$-40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	P-20A

<sup>\*</sup>N = Plastic DIP; R = 0.15" Small Outline IC (SOIC);

P = Plastic Leaded Chip Carrier (PLCC).

## ADG211A/ADG212A—Typical Performance Characteristics

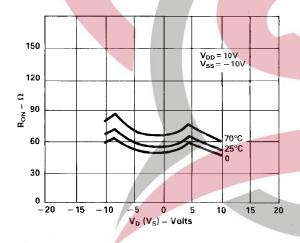
The switches can comfortably operate anywhere in the 10V to 15V single or dual supply range, with only a slight degradation in performance. The following graphs show the relevant performance curves. The test circuits and test conditions are given in a following section, "Test Circuits."



150  $V_{DD} = 15V$   $V_{SS} = 0$ 120 Ron - 10 90 70°C 25°C 60 30 0 -20 - 15 10 15 20 VD (Vs) - Volts

Figure 1.  $R_{ON}$  as a Function of  $V_D(V_S)$ : Dual  $\pm 15$  Supplies

Figure 2.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Single + 15V Supply



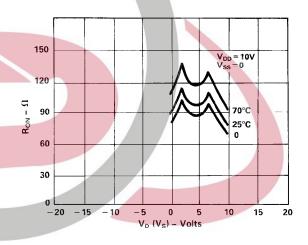
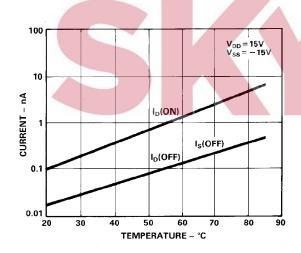


Figure 3.  $R_{ON}$  as a Function of  $V_D(V_S)$ : Dual  $\pm 10V$  Supplies

Figure 4.  $R_{ON}$  as a Function of  $V_D(V_S)$ : Single + 10V Supply



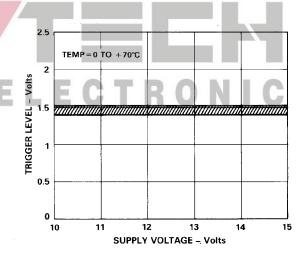


Figure 5. Leakage Current as a Function of Temperature (Note: Leakage Current Reduces as the Supply Voltages Reduce)

Figure 6. Trigger Levels vs. Power Supply Voltage, Dual or Single Supply Voltage

## Typical Performance Characteristics—ADG211A/ADG212A

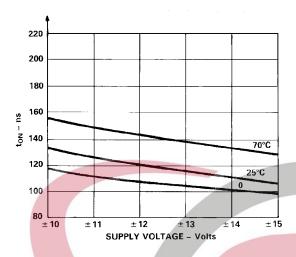


Figure 7. ton vs. Supply Voltage, (Dual Supply)

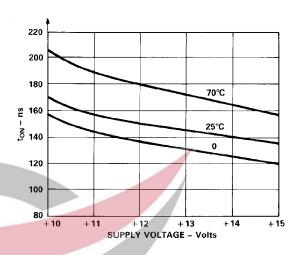


Figure 8. t<sub>ON</sub> vs. Supply Voltage, (Single Supply)

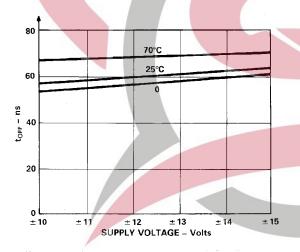


Figure 9. t<sub>OFF</sub> vs. Supply Voltage, (Dual Supply)

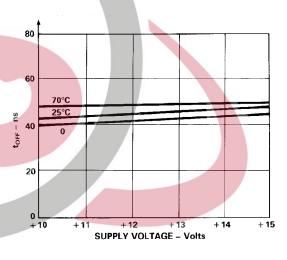


Figure 10. t<sub>OFF</sub> vs. Supply Voltage, (Single Supply)

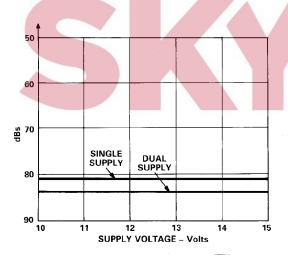


Figure 11. Off Isolation and Channel-to-Channel Crosstalk vs. Supply Voltage

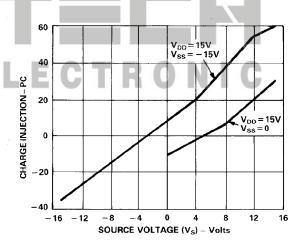


Figure 12. Charge Injection vs. Source Voltage ( $V_S$ ) for Dual and Single 15V Supplies

## **ADG211A/ADG212A**—Typical Performance Characteristics

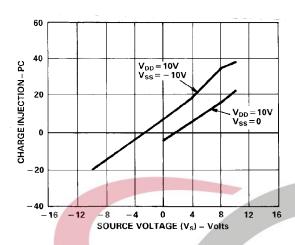


Figure 13. Charge Injection vs. Source Voltage for Dual and Single 10V Supplies

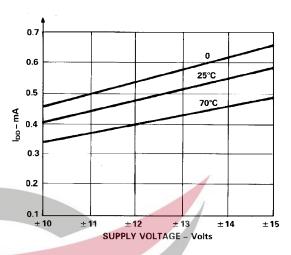


Figure 14. IDD vs. Supply Voltage, (Dual Supply)

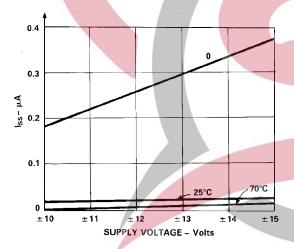


Figure 15. ISS vs. Supply Voltage, (Dual Supply)

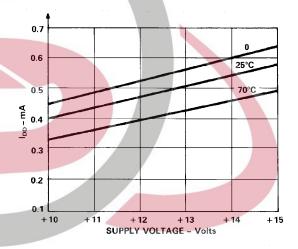


Figure 16. IDD vs. Supply Voltage, (Single Supply)

### TERMINOLOGY

Ron

 $t_{ON}$ 

 $R_{ON}$  Match Difference between the  $R_{ON}$  of any two channels  $I_S$  (OFF) Source terminal leakage current when the switch is off Drain terminal leakage current when the switch is off  $I_D$  (ON) Leakage current that flows from the closed switch into the body

Ohmic resistance between terminals OUT and S

 $V_D(V_S)$  Analog voltage on terminal D, S

 $\begin{array}{ll} C_S \, (OFF) & \text{Switch input capacitance "OFF" condition} \\ C_D \, (OFF) & \text{Switch output capacitance "OFF" condition} \\ C_{IN} & \text{Digital input capacitance} \end{array}$ 

C<sub>D</sub>, C<sub>S</sub> (ON) Input or output capacitance when the switch

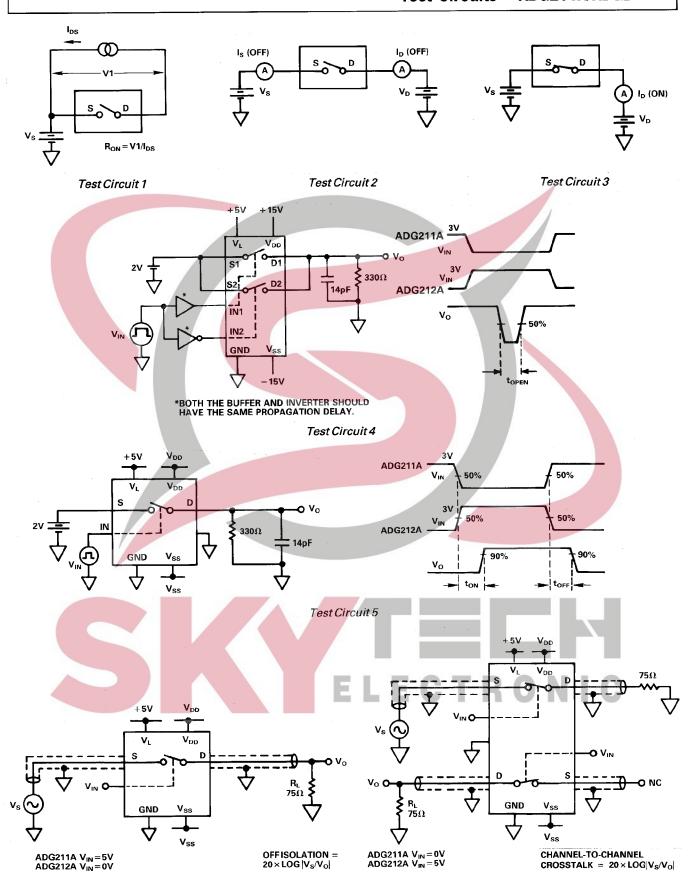
Delay time between the 50% and 90% points of the digital input and switch "ON" condition t<sub>OFF</sub>

Delay time between the 50% and 90% points of the digital input and switch "OFF" condition "OFF" time measured between 50% points of both switches, which are connected as a multiplexer, when switching from one address state to another

 $\begin{array}{lll} V_{INL} & & \text{Maximum Input Voltage for a Logic Low} \\ V_{INH} & & \text{Minimum Input Voltage for a Logic High} \\ I_{INL} \left( I_{INH} \right) & & \text{Input current of the digital input} \end{array}$ 

 $\begin{array}{lll} V_{\rm DD} & & & & & & \\ V_{\rm DD} & & & & & & \\ V_{\rm SS} & & & & & \\ V_{\rm SS} & & & & & \\ V_{\rm L} & & & & \\ L_{\rm Ogic} & & & & \\ L_{\rm DD} & & & & \\ Positive & & & \\ L_{\rm SS} & & & & \\ N_{\rm Cgative} & & & \\ L_{\rm SS} & & & \\ \end{array}$ 

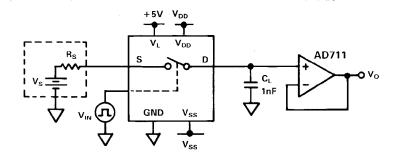
## Test Circuits—ADG211A/ADG212A

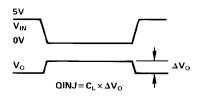


Test Circuit 6. Off Isolation

Test Circuit 7. Channel-to-Channel Crosstalk

### ADG211A/ADG212A





Test Circuit 8. Charge Injection

### **OUTLINE DIMENSIONS**

Dimensions shown in inches and (mm).

### 16-Pin Plastic (N-16)

### 16-Lead Narrow Body SOIC (R-16A)

